

### **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The series of devices uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **Application**

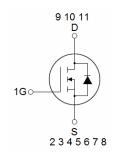
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

#### **General Features**

- $V_{DS}$  =150V, $I_D$  =170A  $R_{DS(ON)}$ =5.0m $\Omega$  , typical@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





**Schematic Diagram** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP15T14LL	NCEP15T14LL	TOLL	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	150	V	
Gate-Source Voltage	V <sub>G</sub> s	±20	V	
Drain Current-Continuous (T <sub>C</sub> =25℃)	I <sub>D</sub> (T <sub>C</sub> =25°ℂ)	170	Α	
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (T <sub>C</sub> =100℃)	120	A	
Drain Current-Continuous (T <sub>A</sub> =25℃)	I <sub>D</sub> (T <sub>A</sub> =25℃)	16	А	
Pulsed Drain Current (Note 1)	I <sub>DM</sub>	680	А	
Maximum Power Dissipation ( $T_C$ =25 $^{\circ}$ C)	P <sub>D</sub> (T <sub>C</sub> =25°C)	380	W	
Maximum Power Dissipation (T <sub>A</sub> =25°C)	P <sub>D</sub> (T <sub>A</sub> =25°C)	3.75	W	
Derating factor		2.5	W/℃	
Single pulse avalanche energy (Note 5)	Eas	E <sub>AS</sub> 1300		
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	℃	

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	0.4	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	40	°C/W

### Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics				- 71-		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	150		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						l
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =85A	-	5	5.8	mΩ
Gate resistance	R <sub>G</sub>	F=1.0MHz	-	5.0	-	Ω
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =85A	70	-	-	S
Dynamic Characteristics (Note4)			•	ı		
Input Capacitance	C <sub>lss</sub>		-	5500	7150	PF
Output Capacitance	Coss	$V_{DS}$ =75V, $V_{GS}$ =0V,	-	690	890	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	24	31	PF
Switching Characteristics (Note 4)						•
Turn-on Delay Time	t <sub>d(on)</sub>		-	26	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =75 $V$ , $I_{D}$ =85 $A$	-	36	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =10 $V$ , $R_{G}$ =4.7 $\Omega$	-	47	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	15	-	nS
Total Gate Charge	Qg	\/ 75\/\ 05A	-	80	104	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=75V,I_{D}=85A,$	-	32	41	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	22	28	nC
Drain-Source Diode Characteristics						•
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>F</sub> =85	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	170	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = I_S$	-	146		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	485		nC
-					1	·

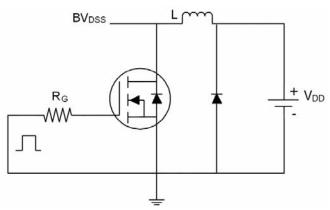
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A$  =25° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V  $_{DD}$  =50 V,V  $_{G}$  =10 V,L=0.5 mH,Rg=25  $\Omega$

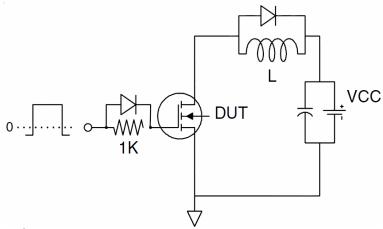


### **Test Circuit**

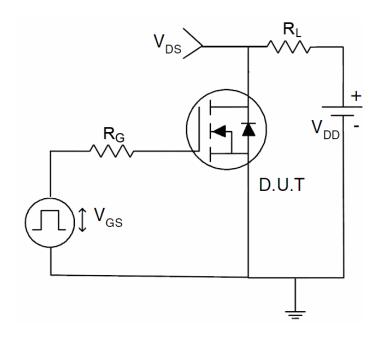
### 1) E<sub>AS</sub> test Circuit



### 2) Gate charge test Circuit

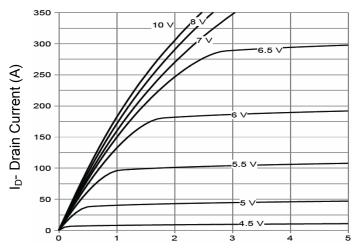


#### 3) Switch Time Test Circuit



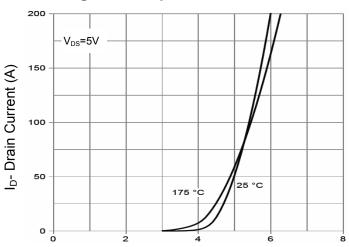


### **Typical Electrical and Thermal Characteristics**



Vds Drain-Source Voltage (V)

**Figure 1 Output Characteristics** 



Vgs Gate-Source Voltage (V)

**Figure 2 Transfer Characteristics** 

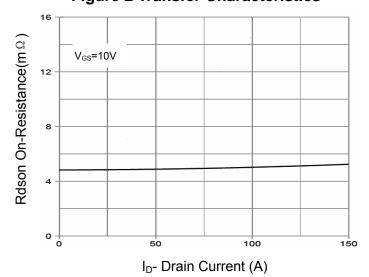
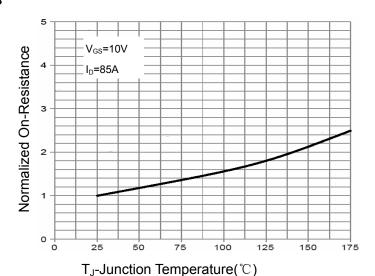


Figure 3 Rdson- Drain Current



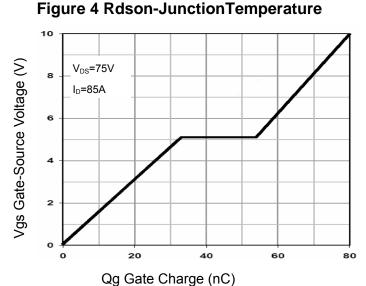
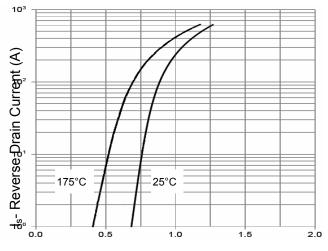


Figure 5 Gate Charge

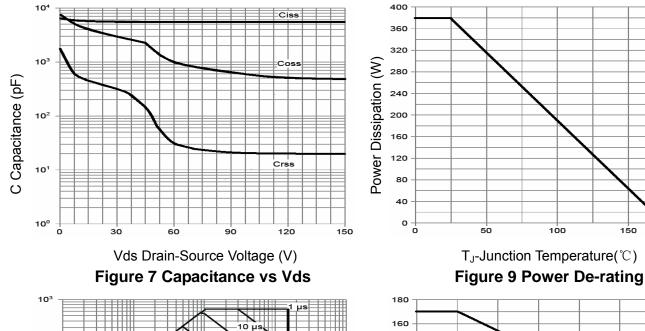


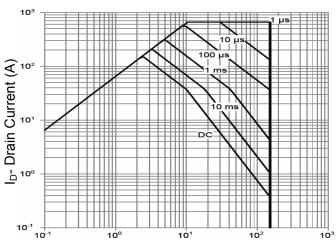
Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

200







Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

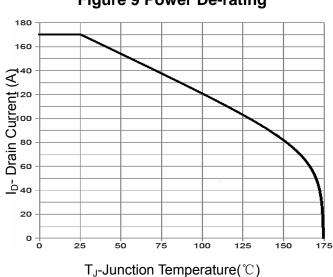
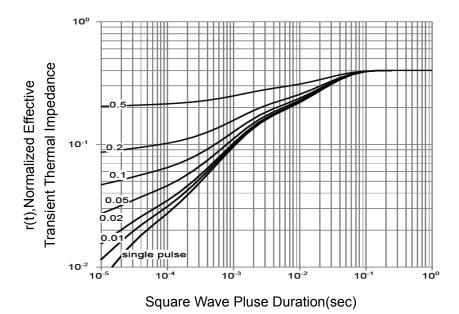


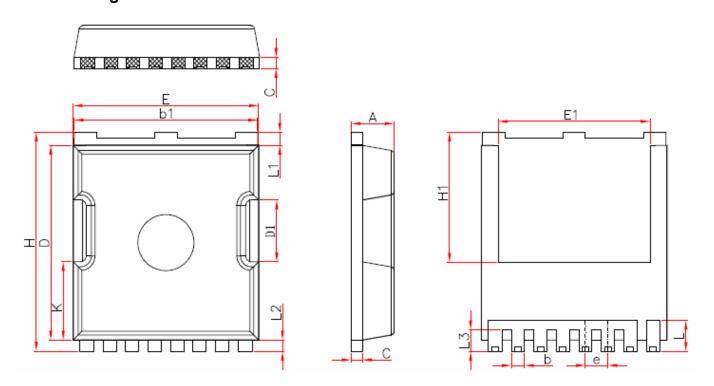
Figure 10 Current De-rating



**Figure 11 Normalized Maximum Transient Thermal Impedance** 



# **TOLL Package Information**



Symbol	Millimeters			
	Min.	Nom.	Max.	
A	2.20	2.30	2.40	
b	0.65	0.75	0.85	
b1	9.70	9.80	9.90	
С	0.50	0.60	0.70	
D	10.30	10.40	10.50	
D1	3.15	3.3	3.45	
Е	9.70	9.90	10.10	
E1	8.00	8.10	8.20	
е	1.10	1.20	1.30	
Н	11.6	11.7	11.8	
H1	6.85	6.95	7.05	
K	4.08	4.18	4. 28	
L	1.60	1.65	2.10	
L1	0.60	0.70	0.80	
L2	0.50	0.60	0.70	
L3	1.05	1.20	1.30	

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# NCEP15T14LL

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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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PJMF280N60E1\_T0\_00201 PJMF600N65E1\_T0\_00201 PJMF900N65E1\_T0\_00201